

ABSTRACT OF THE INVENTION

The method of fabricating a nitride semiconductor device of this invention includes plural steps of respectively growing plural nitride semiconductor layers on a substrate; and between
5 a step of growing one nitride semiconductor layer and a step of growing another nitride semiconductor layer adjacent to the one nitride semiconductor layer among the plural steps, a step of changing a growth ambient pressure from a first growth ambient pressure to a second growth ambient pressure different from the
10 first growth ambient pressure.